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[Vishay/Siliconix](#)
[SI3467DV-T1-E3](#)

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Si3467DV
 Vishay Siliconix

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY		
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
- 20	0.054 at V _{GS} = - 10 V	- 5.0
	0.094 at V _{GS} = - 4.5 V	- 3.8

FEATURES

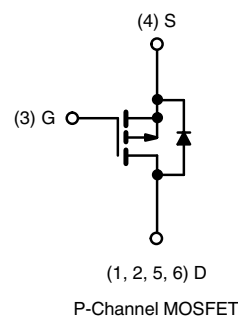
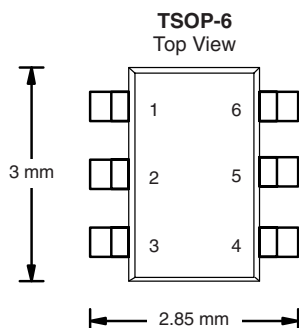
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
 COMPLIANT
 HALOGEN
FREE
 Available

APPLICATIONS

- Load Switch
 - PC
 - Game Machine



Ordering Information: Si3467DV-T1-E3 (Lead (Pb)-free)
 Si3467DV-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code: 7Cxxx

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	5 s	Steady State	Unit
Drain-Source Voltage	V _{DS}	- 20		V
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T _J = 150 °C) ^a	I _D	T _A = 25 °C	- 5.0	- 3.8
		T _A = 70 °C	- 3.9	- 3.0
Pulsed Drain Current	I _{DM}	- 25		A
Continuous Source Current (Diode Conduction) ^a	I _S	- 1.7	- 0.95	
Maximum Power Dissipation ^a	P _D	T _A = 25 °C	2.0	1.14
		T _A = 70 °C	1.3	0.73
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 5 s	50	62.5	°C/W
		Steady State	90	110	
Maximum Junction-to-Foot (Drain)	R _{thJF}	30	36		

Note:

a. Surface Mounted on 1" x 1" FR4 board.

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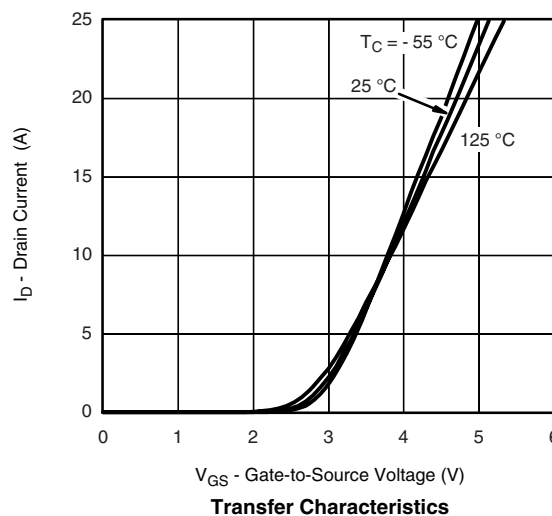
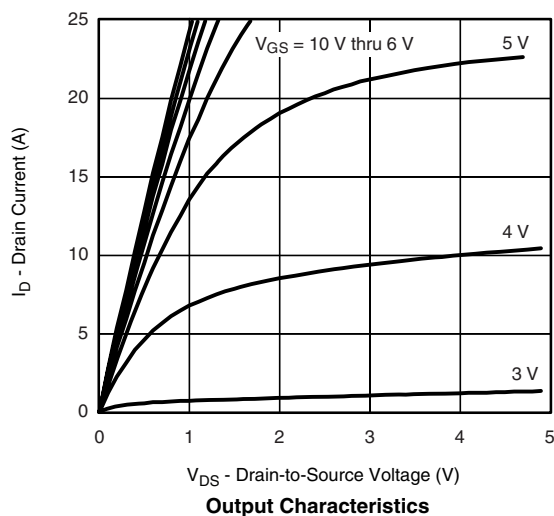
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-1.0		-3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -10\text{ V}$	-25			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -5\text{ A}$		0.042	0.054	Ω
		$V_{GS} = -4.5\text{ V}, I_D = -1.1\text{ A}$		0.073	0.094	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -5\text{ A}$		10		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.7\text{ A}, V_{GS} = 0\text{ V}$		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -10\text{ V}, I_D = -5.0\text{ A}$		8.7	13	nC
Gate-Source Charge	Q_{gs}			1.7		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$		9		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -10\text{ V}, R_g = 6\text{ }\Omega$		10	15	ns
Rise Time	t_r			15	25	
Turn-Off Delay Time	$t_{d(off)}$			22	35	
Fall Time	t_f			18	30	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		20	40	

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- b. Guaranteed by design, not subject to production testing.

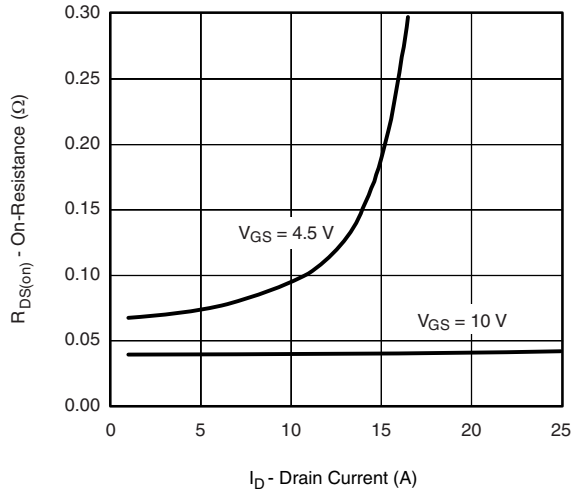
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

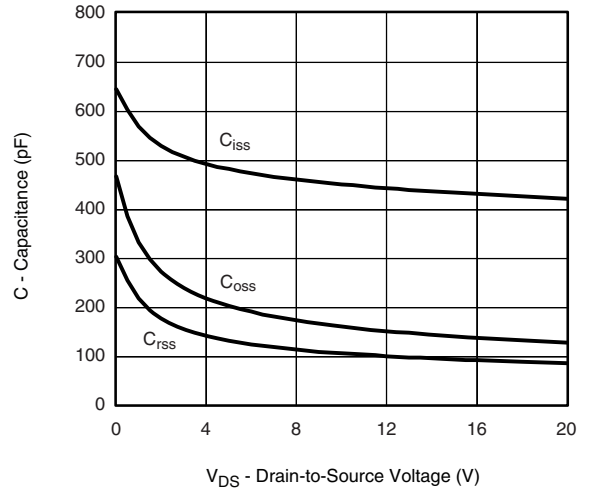




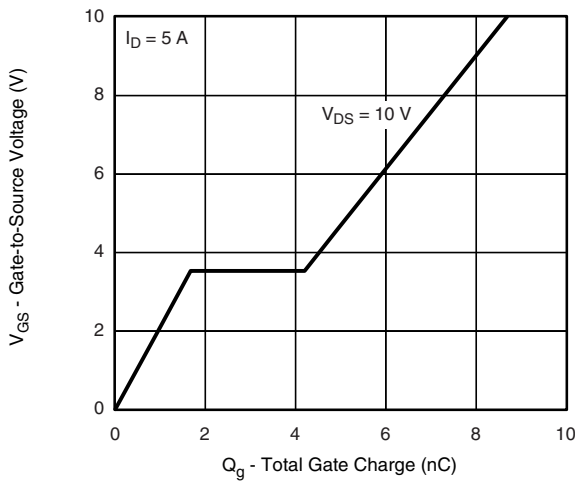
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



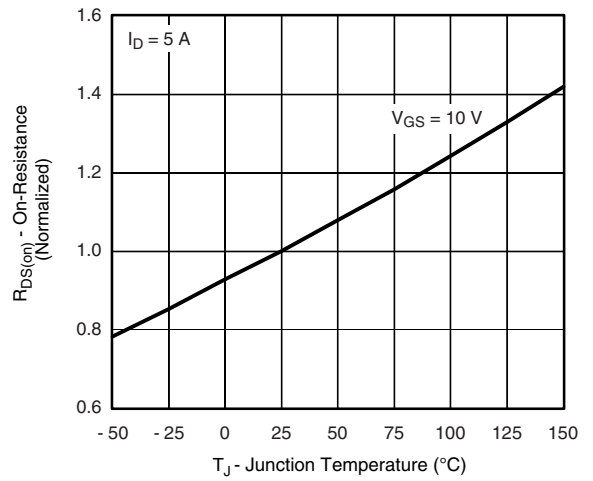
On-Resistance vs. Drain Current



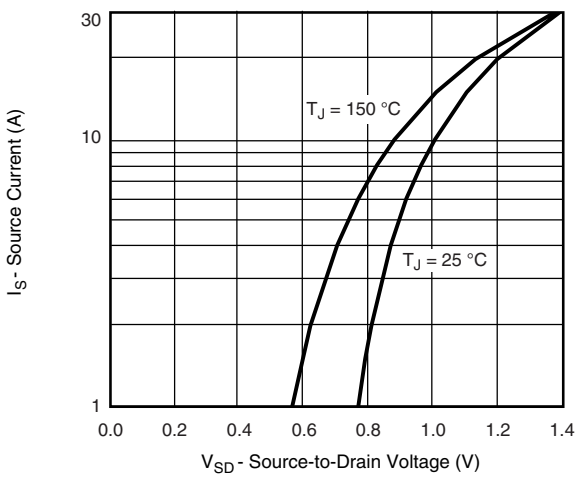
Capacitance



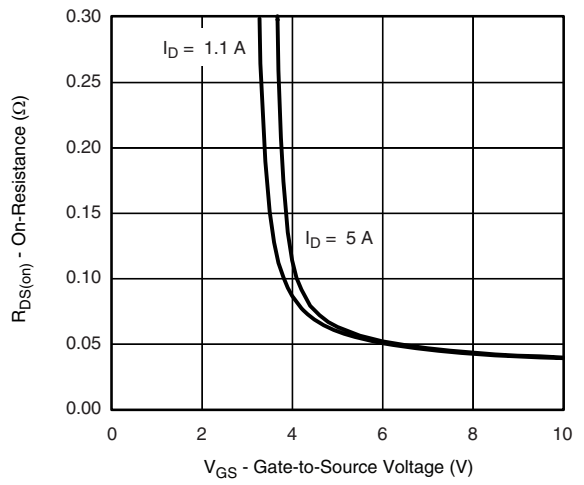
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



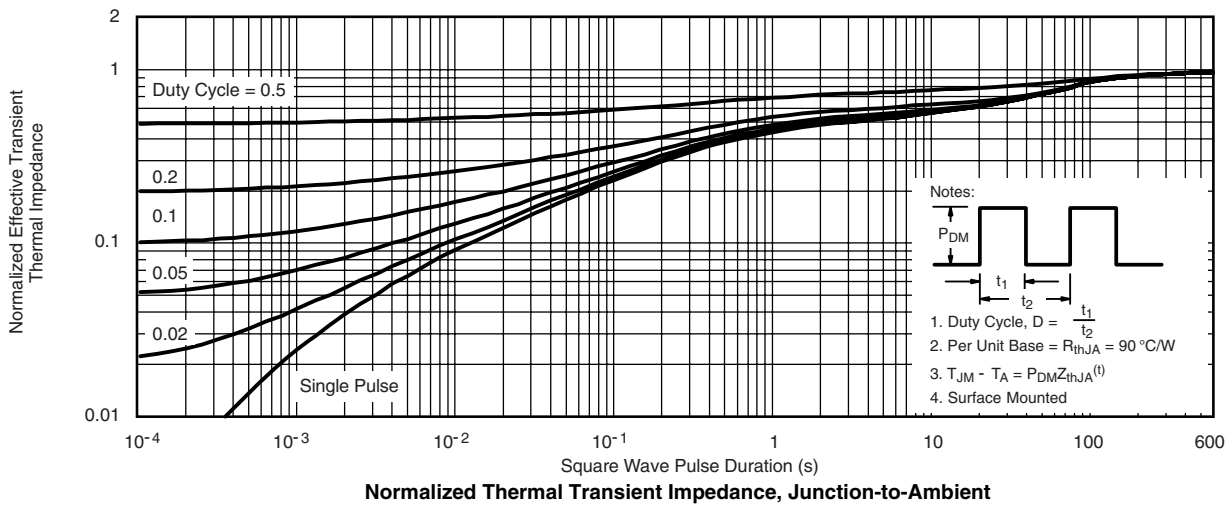
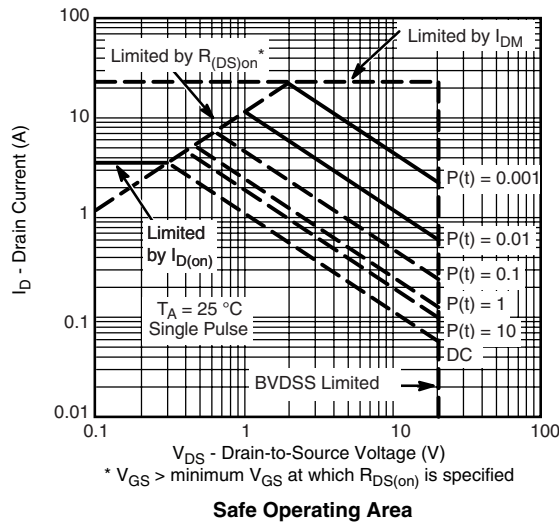
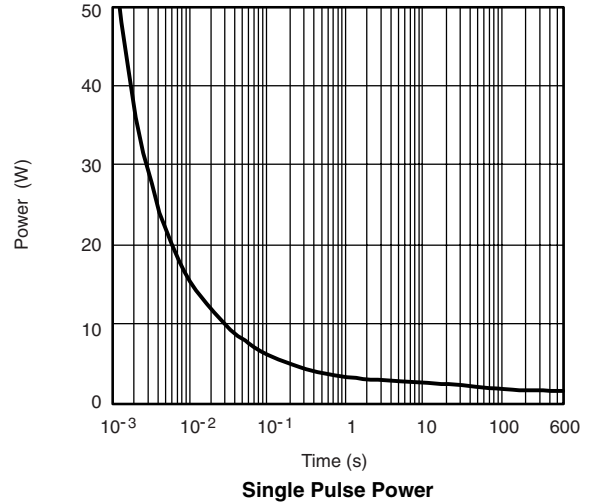
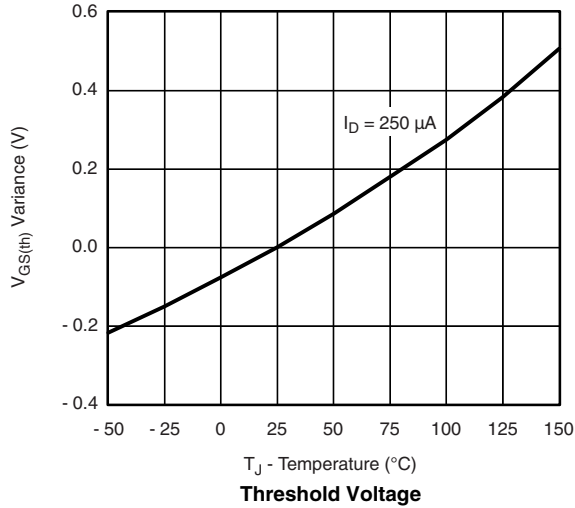
On-Resistance vs. Gate-to-Source Voltage

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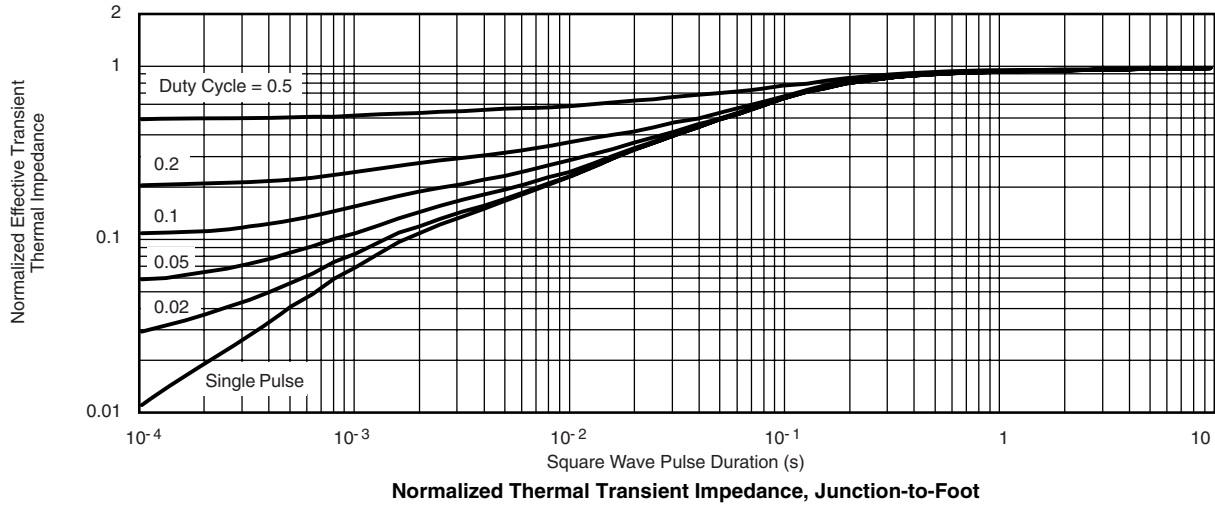
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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